

2SC1471  
TO3 Silicon NPN High Voltage Switching Transistor

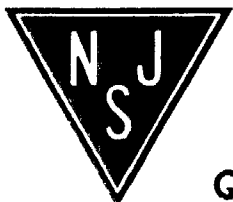
SPECIFICATION

GENERAL DESCRIPTION:

**ELECTRICAL CHARACTERISTICS – CARACTÉRISTIQUES ÉLECTRIQUES \*\***

SYMBOLS	Min	Typ	Max	UNIT	TEST CONDITIONS – CONDITIONS DE MESURE
<b>OFF CHARACTERISTICS – CARACTÉRISTIQUES A L'ÉTAT BLOQUÉ</b>					
$V_{CE0sat}$	400			V	$I_B = 0, I_C = 0,2 A, L = 25 mH$
$V_{(BR)EBO}$	7		30	V	$I_C = 0, I_B = 0,1 A$
$I_{CEX}$			0,4 4	mA	$T_{case} = 25^{\circ}C$ $T_{case} = 125^{\circ}C$ $V_{CE} = V_{CEX}, V_{BE} = -2,5 V$
$I_{CER}$			1 8	mA	$T_{case} = 25^{\circ}C$ $T_{case} = 125^{\circ}C$ $V_{CE} = V_{CEX}, R_{BE} \leq 5 \Omega$
$I_{EBO}$			2	mA	$I_C = 0, V_{EB} = 5 V$
<b>ON CHARACTERISTICS – CARACTÉRISTIQUES A L'ÉTAT CONDUCTEUR</b>					
$V_{CEsat}^*$			1,5	V	$I_C = 20 A, I_B = 4 A$ $I_C = 30 A, I_B = 8 A$
			1,5 5	V	$I_C = 16 A, I_B = 3,2 A$ $I_C = 24 A, I_B = 5 A$
$V_{BEsat}^*$			1,6	V	$I_C = 20 A, I_B = 4 A$ $I_C = 16 A, I_B = 3,2 A$
<b>DYNAMIC CHARACTERISTICS – CARACTÉRISTIQUES DYNAMIQUES</b>					
$f_T$		5		MHz	$f = 1 MHz, I_C = 1 A, V_{CE} = 10 V$
$C_{22b}$		500		pF	$f = 1 MHz, V_{CE} = 10 V$

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**TYPICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

